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(A)

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10-2004-0022938
2004 03 18

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10-2002-0054536

(22)

2002 09 10

(71)

.

20

(72)

3 1407-77

(74)

:

(54)

, 가 , ,
.

6

1 .

2 1 'A-A" .

3a 3e 2 .

4a 4b .

5 .

6 5 'B-B" .

7a	7e	6
8a	8c	7d

< >

1,31 : 2,32 :

4,34 : 6,36 :

8,38 : 10,40 :

12,42 : 14,44 :

16,46 : 18,48 :

20,50 : 22,52 :

24 : 26 :

56 :

가

(Thin Film Transistor; TFT)

1 2 (10) (22) (4) (2) (2) TFT(TP) , TFT(TP)

P) (SP) .

TFT(TP) (2) (6), (4) (8) (20)

(22) (10) . , TFT(TP) (6)

(8) (10) (14,16) . TFT(TP)

(2) (4) (2)

2) .

(22) (4) (2) (20)

(22) (1)

() () . (22)

18) (2) , (SP) (22) (24) (SP) (24) (

(26) (22) .

3a 3e .

(1) 3a (2)

(6) (2) (6) (1) 1 (14)

(12) (12) 1 2 (18)

(16) (12) (10) 2 (18)

(4), (24), (8) (20) (26) (18)

(1) (22) .

(SP) (12)

(24) (2) . ,

(24) .

4a 4b (12) (18) (24)

(2) (22) . ,

(12) (2) (24) (22)

(12) (18) 가 (2,22) 4b (18)

(18) , 4a (18) 가 (18)

가 (SP) .

1

2

0~70%

5 8c

5 6 , (31) (34) (32) T

FT(TP) , TFT (TP) (40) (52) , (52) (32)

(SP)

TFT(TP) (32) (36), (34) (38) (50)

(52) (40) , TFT(TP) (36)

TFT(TP) (38) (40) (44,46)

(32) (34)

(52)

(34) (32)

(52) (50)

() () () (31)

(52)

(SP) (52) (SP)

(32) , (32) (42) (52)

(52) (48) (56) (42)

(SP) (42) (32) (52)

(SP)

(SP) (42) 가 (32) (52)

(SP)

7a 7e 6

7a , (31) (32) (36)

(31) (sputtering)

(Al) , 1 ()

(31) (32) (36)

7b , (32) (36) (31) (42), (44)

(46)

(SiNx) (32) (36) (31) (SiOx)

(42) (42) 1 2

(Chemical Vapor Deposition)

1 N P

() 2 (Dry Etching) 2

(44) (46) .

7c (44) (46) (31) (34), (

38,40) .

(44) (46) (31) CVD (sputtering)

(Cr) (Mo) . ,

(34), (38) (40) (38) (40)

(46) (46) (44) (38,40) (36)

7d (38) (40) (31) (48) .

(38) (40) (31) (48)

(48) (Acryl) , BCB(benzocyclobutane), PFCB(perfluorocyclobutane)

(SiNx), (SiOx) . 4 (

0) (56) (48) (5) (

(50) (48) (40) 가 (56) (4

8) (32) (42) 가 . (

56) (50) .

7e (48) (31) (52) .

(48) (sputtering)

(Indium-Tin-Oxide : ITO), - - (Indium-Zinc-Oxide : IZO) -

(Indium-Tin-Zinc-Oxide : ITZO) , 5 ()

(52)

(52) (48) (50) (40) . ,

(48) (56) (42) (42)

(32) (SP) .

8a 8c 7d .

8a (48) (31) (60) . ,

(31) 4 (68)가 (64) (S1) , 4 (68)

(62) (S3) (62) (66)

, 4 (68) (S2)

8b , 4 (68) 4 (68) (S2)

(70) (S1) (70) 4 (68) (66)

1 (70a) 1 , 4 (68) (64)

2 (70b) 1 2 .

8c (70) (48) . ,

(48) (50) (56) .

(50) (48) 가 (40)

(48) (40) (56) (48) (42)

가 , (56) (70b) 가

(42) (48) .

5.

4

1

2

1

6.

5

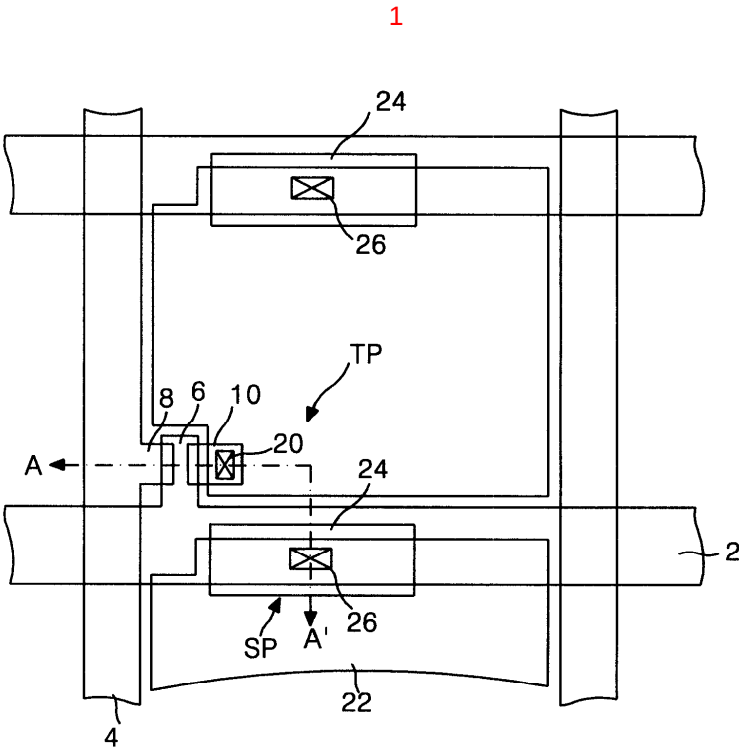
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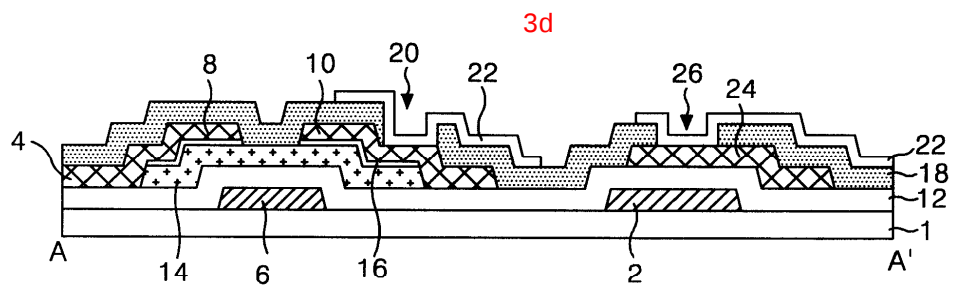
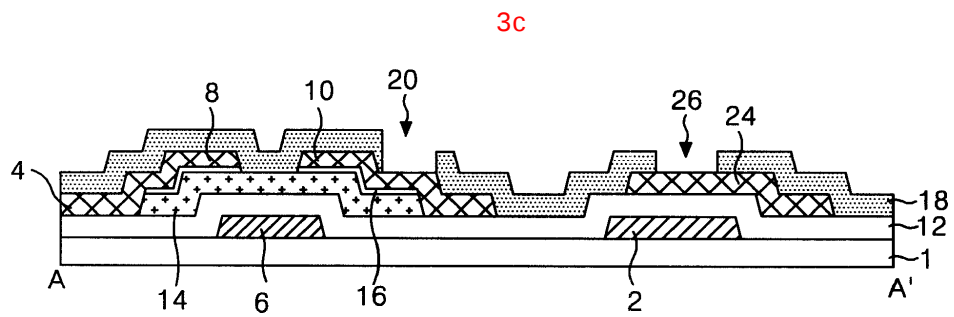
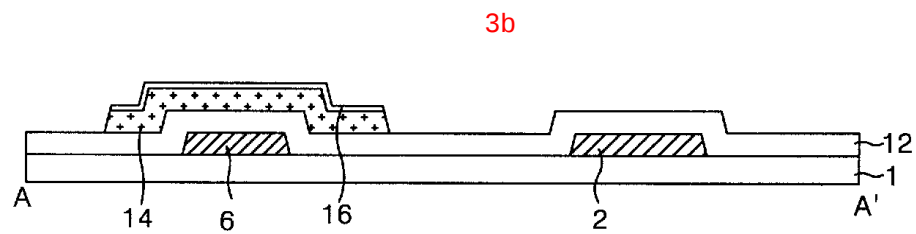
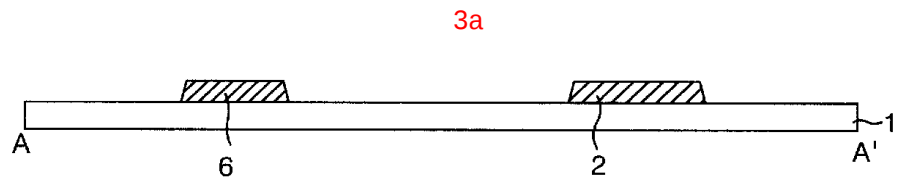
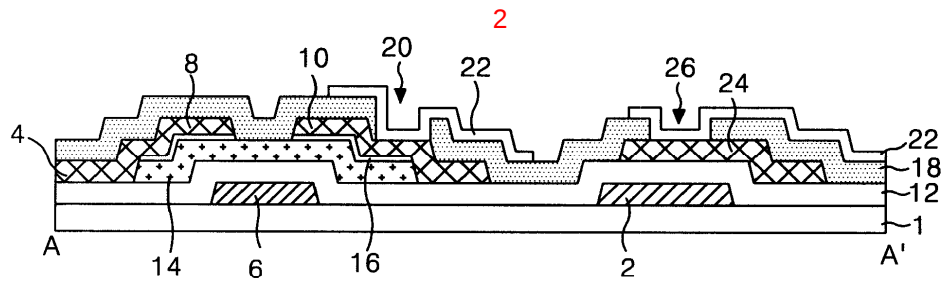
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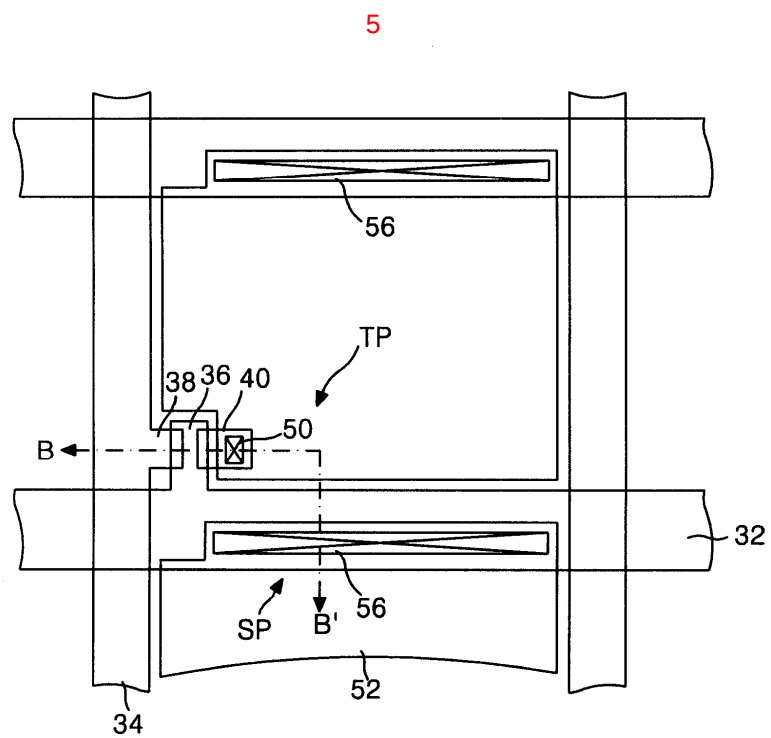
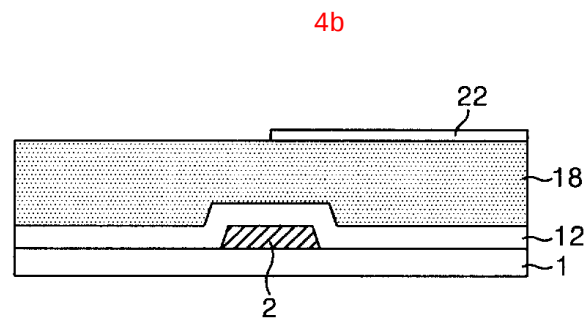
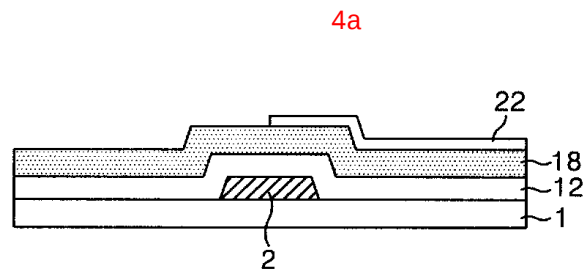
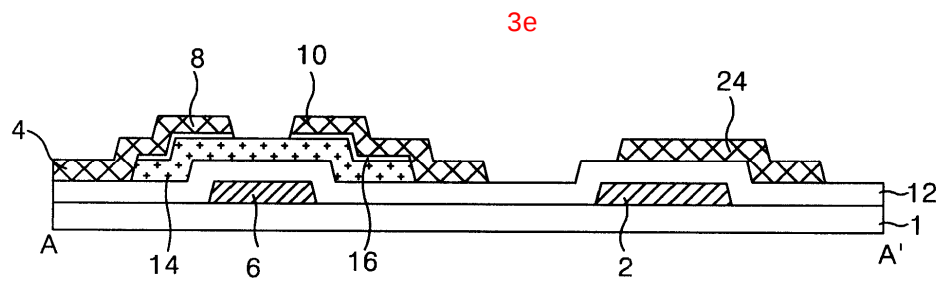
7.

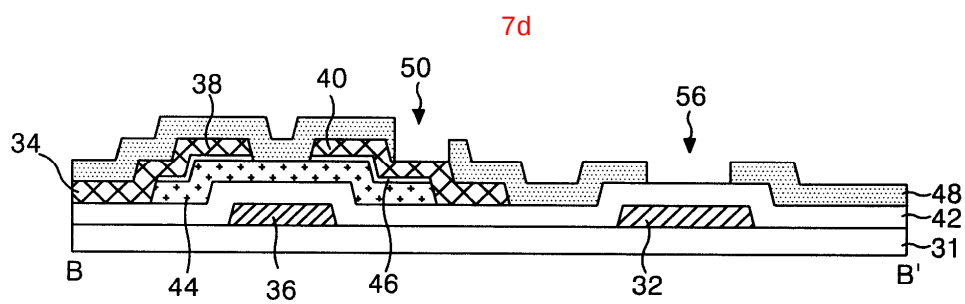
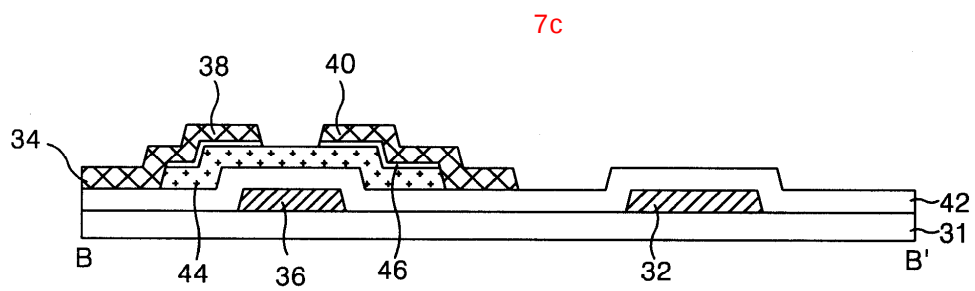
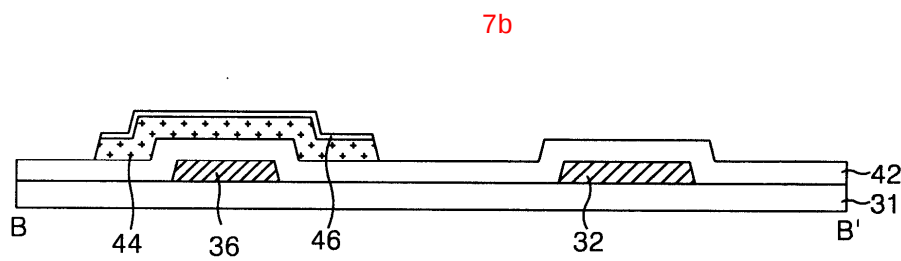
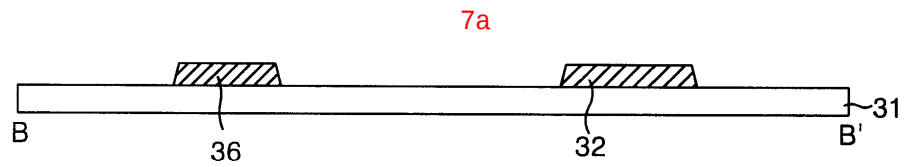
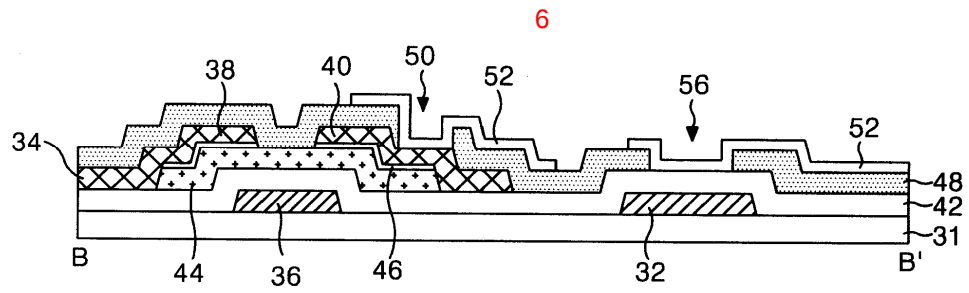
4

0~70%

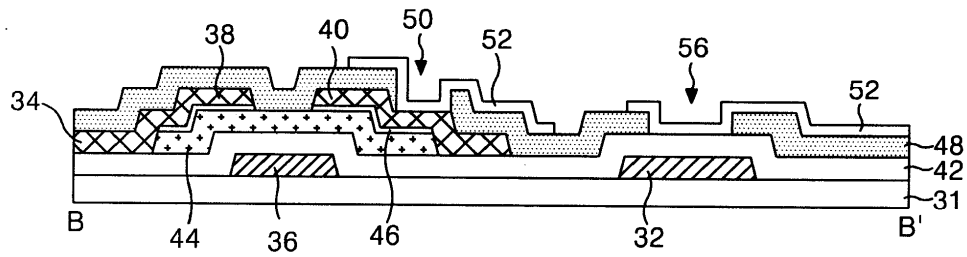




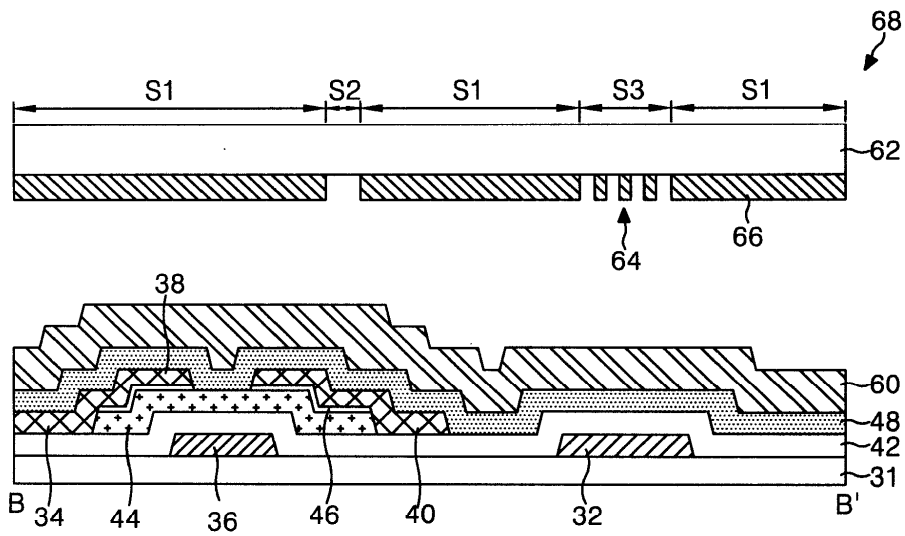




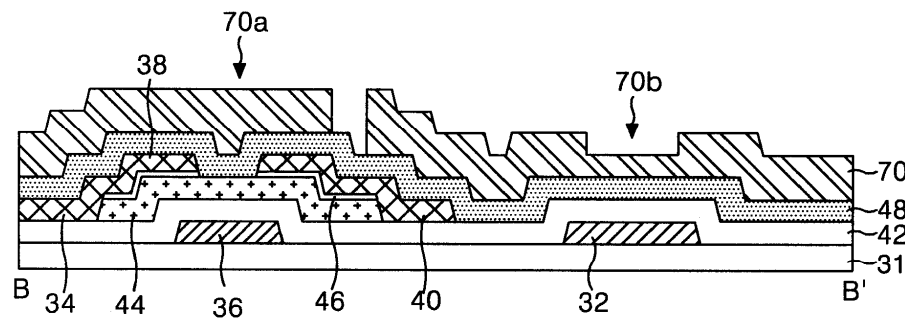
7e



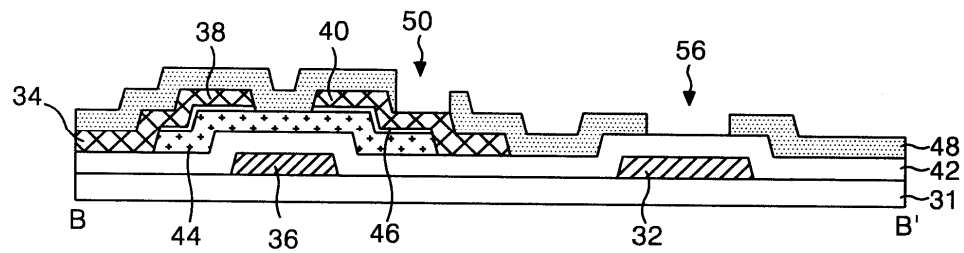
8a



8b



8c



专利名称(译)	液晶显示元件的制造方法		
公开(公告)号	KR1020040022938A	公开(公告)日	2004-03-18
申请号	KR1020020054536	申请日	2002-09-10
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG显示器有限公司		
当前申请(专利权)人(译)	LG显示器有限公司		
[标]发明人	LEE JAEGU		
发明人	LEE,JAEGU		
IPC分类号	G02F1/13 H01L27/12 H01L21/84 H01L21/77 H01L27/13		
CPC分类号	H01L27/13 H01L27/1288 H01L27/1214 H01L27/12 H01L27/1255		
其他公开文献	KR100886241B1		
外部链接	Espacenet		

摘要(译)

液晶显示装置的制造方法技术领域本发明涉及能够提高存储电容器的电容值的液晶显示装置的制造方法。根据本发明的另一方面，提供一种制造液晶显示装置的方法，包括在栅极线和数据线彼此交叉的区域中形成薄膜晶体管，形成保护膜以覆盖其上形成有薄膜晶体管的基板，形成通孔和漏极接触孔，并形成分别通过通孔和漏极接触孔与薄膜晶体管的栅极绝缘膜和漏极接触的像素电极而且，其特征在于。 6

